

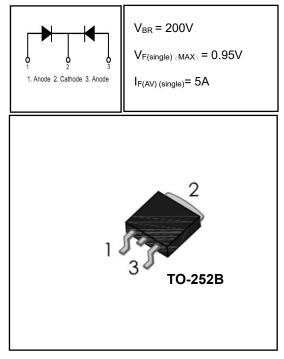
10A 200V SchottkyBarrierDiode

1 Description

Dual center tab Schottky rectifier suited for High Frequency server and telecom base station SMPS. Packaged in TO Inside the package, this device combineshigh current rating and low volume to enhance both reliability and power density of the application.

2 Features

- High junction temperature capabiliy
- Low leakage current
- Low thermal resistance
- High frequency operation
- Avalanche specification
- **3** Applications
- Switching Power Supply
- Power Switching Circuits
- General Purpose



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage		V _{RRM}	200	V
RMS Reverse Voltage		V _{R(RMS)}	160	V
DC Blocking Voltage		VR	200	V
Average Rectified Forward Current(single)			5	Α
Average Rectified Forward Current(double)		I _{F(AV)}	10	Α
Repetitive Peak Surge Current(single)		I _{FRM}	10	Α
Nonrepetitive Peak Surge Current(single)	tp=8.3ms	I _{FSM}	120	Α
Avalanche Energy(single) L=1mH		E _{AS}	15	mJ
Operating Junction Temperature Range		Tj	-55~150	°C
Storage Temperature Range		T _{stg}	-55~150	°C

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	RthJC	2.0	°C /W



MBR10200CT

1.3 Electrical Characteristics (IC=25 C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Instantaneous	VF	$I_F = 5A$	-	0.85	0.95	V
Forward Voltage		I _F = 5A, T _C = 125℃	-	-	0.83	V
		I _F = 10A	-	0.97	1.20	V
Maximum Instantaneous	I _R	V _R = 200V	-	5	50	uA
Reverse		V _R = 200V, T _C = 125℃	-	-	10	mA
Total capacitance	Ctot	V _R =0V f=1MHz	-	58	-	pF
DC Blocking Voltage	VBR	I _R =100uA	200	240	-	V

4.3 Electrical Characteristics (Tc=25°C,unless otherwise noted)

DEFINITIONS

VF = Instantaneous forward voltage (pw = 300µs, D = 2%).

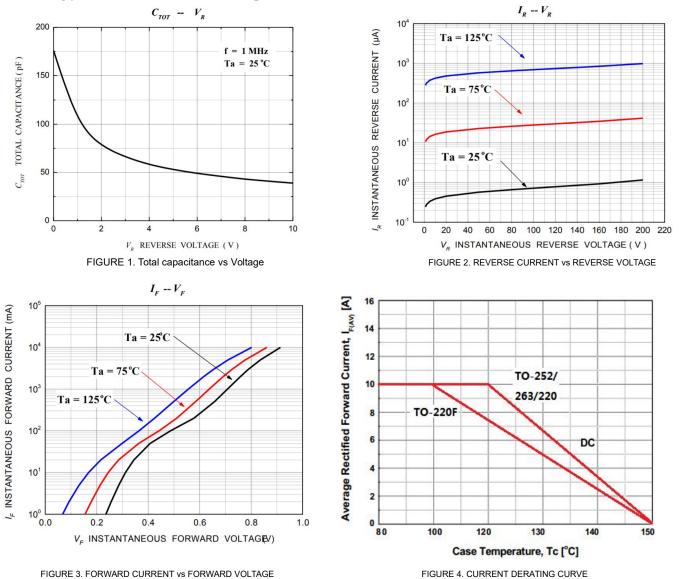
IR = Instantaneous reverse current.

 $R\theta JC$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

5 Typical characteristics diagrams





6 Typical Test Circuit and Waveform

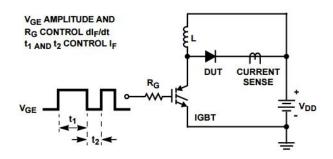


FIGURE 5. trr TEST CIRCUIT

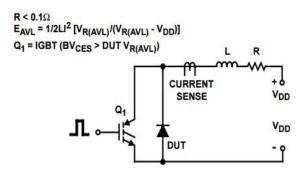


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT FIGURE

FIGURE 6. trr WAVEFORMS AND DEFINITIONS

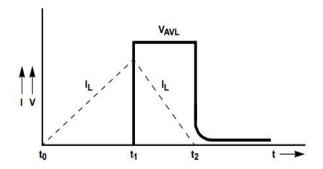
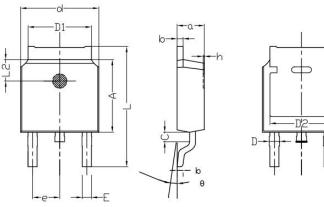


FIGURE8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

7 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MBR10200CT	TO-252B	MBR10200CT	Pb-free	Braid	2500/disc





0 1 1	Dimensions In	Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
а	2.20	2.40	0.087	0.095
b	0.46	0. 58	0.018	0.023
с	0.70	0.90	0.028	0.035
D	0.80	1.10	0.032	0.043
d	6.30	6.70	0.248	0.264
D1	5.00	5. 50	0.197	0.217
D2	TYP 5.346		TYP 0.210	
A	5.80	6.20	0.228	0.244
е	2.19	2.39	0.086	0.094
L	9.40	10.40	0.370	0.409
В	2.6	<mark>3.</mark> 2	0.102	0.126
L2	1.5	1.8	0.059	0.071
θ	0	8	0	8
h	0	0.3	0	0.012
V	5.25	5.85	0.207	0.230
Е	0.6	0.8	0.024	0.032

9 Attentions

- Jiangsu Donghai Semiconductor Co., Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under • certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of WXDH products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2023.5.22	1.0	Original	
2023.7.31	1.1	Revise package outlinr dimensions	4 ALL

TO-252B PACKAGE OUTLINE DIMENSIONS